

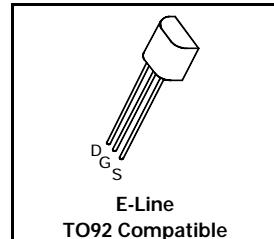
P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

ZVP2110A

FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)}=8\Omega$



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-100	V
Continuous Drain Current at $T_{amb}=25^\circ C$	I_D	-230	mA
Pulsed Drain Current	I_{DM}	-3	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

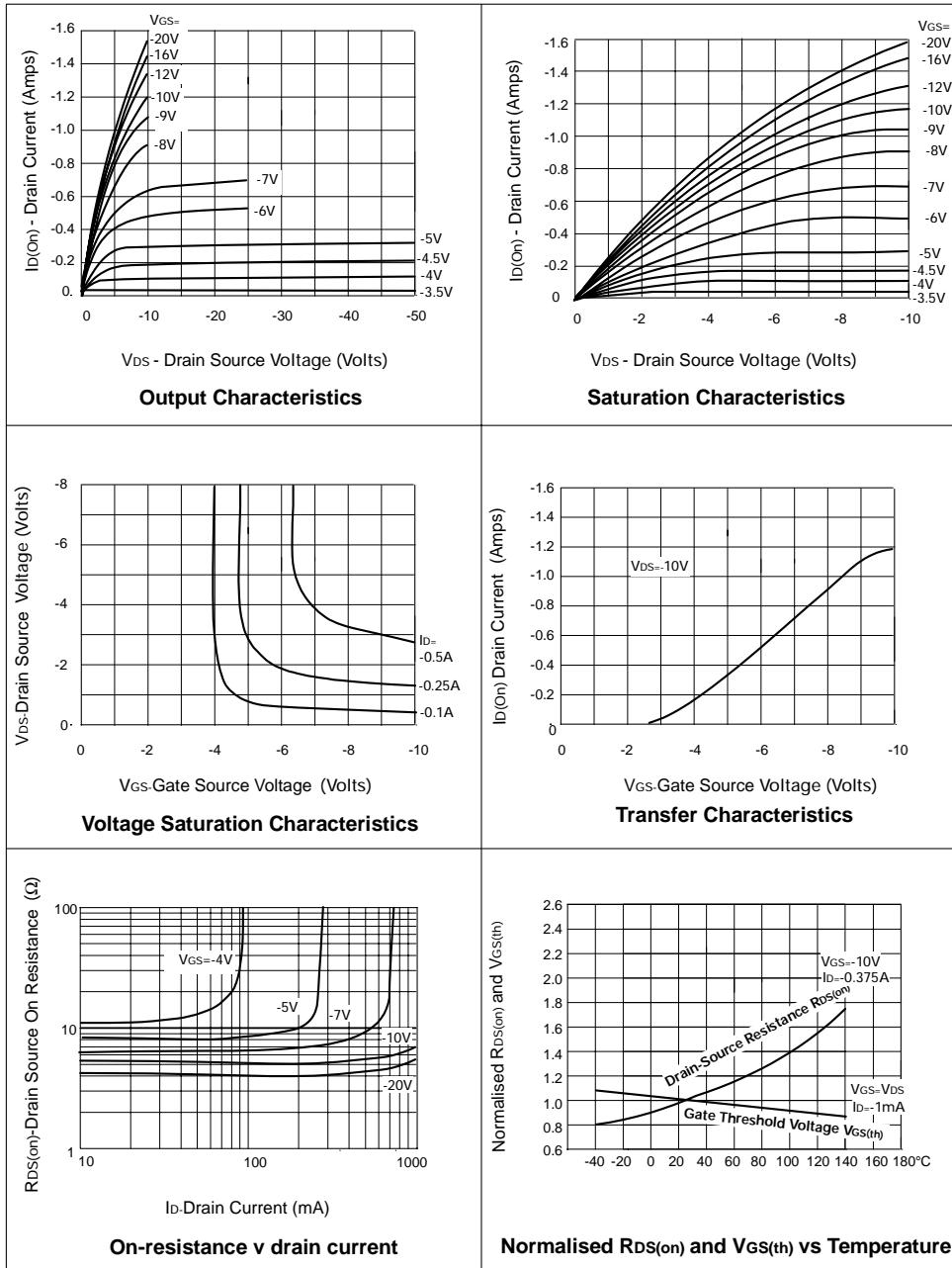
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-100		V	$I_D=-1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	$ID=-1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		-1 -100	μA μA	$V_{DS}=-100 V, V_{GS}=0$ $V_{DS}=-80 V, V_{GS}=0V, T=125^\circ C(2)$
On-State Drain Current(1)	$I_{D(on)}$	-750		mA	$V_{DS}=-25 V, V_{GS}=-10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		8	Ω	$V_{GS}=-10V, I_D=-375mA$
Forward Transconductance (1)(2)	g_{fs}	125		mS	$V_{DS}=-25V, I_D=-375mA$
Input Capacitance (2)	C_{iss}		100	pF	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		35	pF	
Reverse Transfer Capacitance (2)	C_{rss}		10	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	$V_{DD} \approx -25V, I_D=-375mA$
Rise Time (2)(3)	t_r		15	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

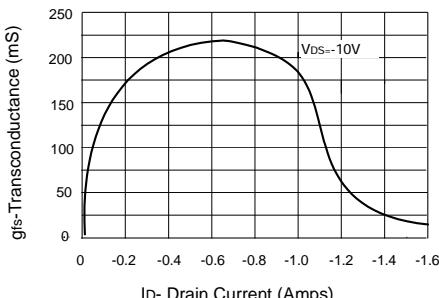
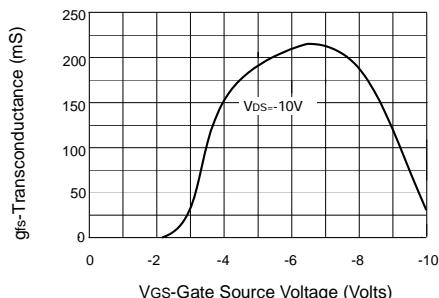
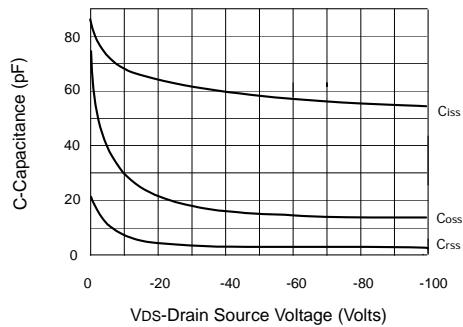
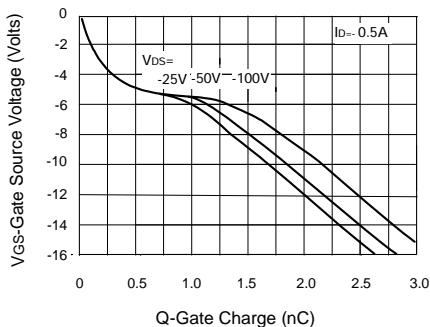
(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2%

(2) Sample test.

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TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS**Transconductance v drain current****Transconductance v gate-source voltage****Capacitance v drain-source voltage****Gate charge v gate-source voltage**